FAIRCHILD SEMICONDUCTOR™

May 2000
ADVANCE INFORMATION

FDS7064A

30V N-Channel PowerTrench® MOSFET

General Description

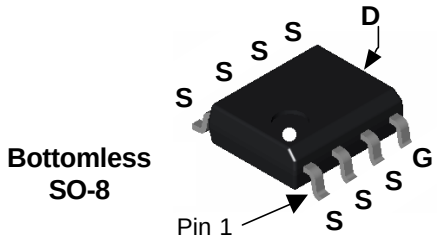
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low $R_{DS(ON)}$ in a small package.

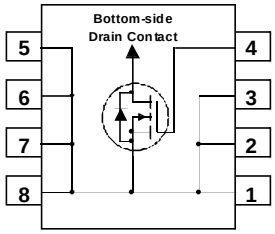
Applications

- Synchronous rectifier
- DC/DC converter

Features

- 19 A, 30 V $R_{DS(ON)}$ = 6.5 mΩ @ V_{GS} = 4.5 V
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability
- Fast switching
- Bottomless™ SO-8 package: Enhanced thermal performance in industry-standard package size





Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	±12	V
I_D	Drain Current – Continuous (Note 1a)	19	A
	– Pulsed	60	
P_D	Power Dissipation for Single Operation (Note 1a)	3.9	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +175	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	38	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS7064A	FDS7064A	13"	12mm	2500 units

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Electrical Characteristics

T_A = 25°C unless otherwise noted

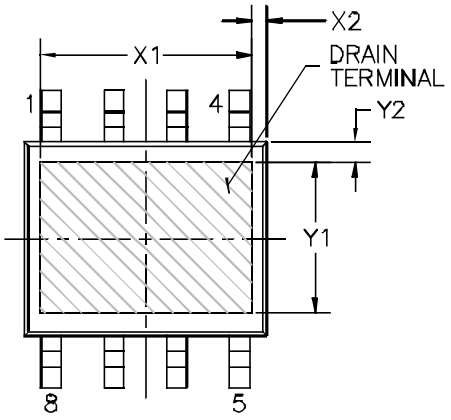
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		20		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	µA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = 12 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = –12 V , V_{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	0.8	1.2	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		-4		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 4.5 V, I_D = 19 A V_{GS} = 10 V, I_D = 21 A			6.5 5.5	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = 4.5 V, V_{DS} = 5 V	50			A
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 19 A		75		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz		5070		pF
C_{oss}	Output Capacitance			550		pF
C_{rss}	Reverse Transfer Capacitance			230		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 10 V, I_D = 1 A, V_{GS} = 4.5 V, R_{GEN} = 6 Ω		17	25	ns
t_r	Turn–On Rise Time			18	25	ns
$t_{d(off)}$	Turn–Off Delay Time			69	100	ns
t_f	Turn–Off Fall Time			29	42	ns
Q_g	Total Gate Charge	V_{DS} = 15 V, I_D = 19 A, V_{GS} = 4.5 V		33	46	nC
Q_{gs}	Gate–Source Charge			7.5		nC
Q_{gd}	Gate–Drain Charge			6.8		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				3.2	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 3.2 A (Note 2)			1.2	V

Notes:

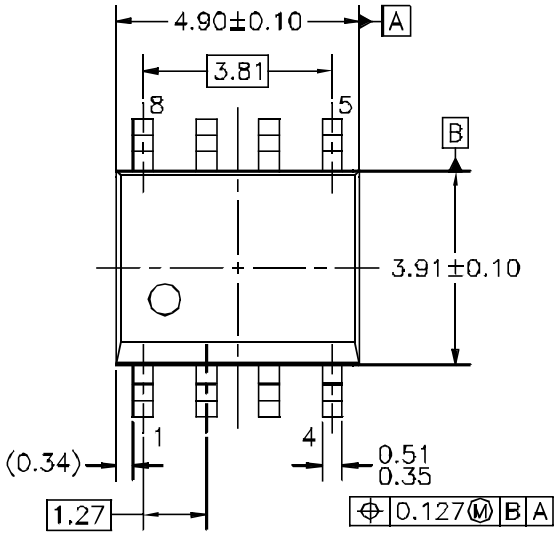
1. $R_{\theta JA}$ is the junction-to-ambient thermal resistance. $R_{\theta JA}$ depends on the user's board design.

a) 38°C/W when mounted on a 1in^2 pad of 2 oz copper

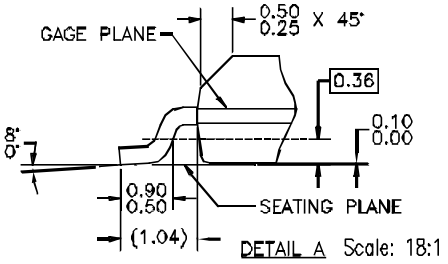
Dimensional Outline and Pad Layout

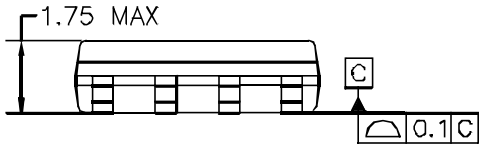


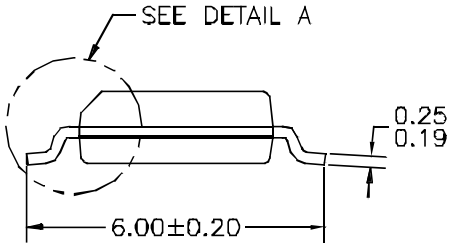
Bottom View

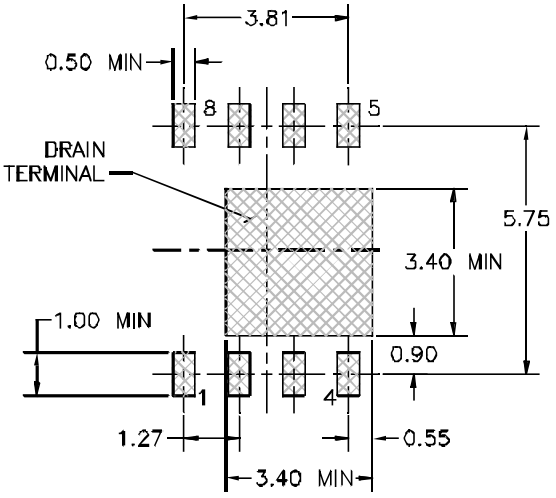


Top View









Minimum Recommended Landing Pattern

Notes: Unless otherwise Specified

a) All dimensions in mm

b) Standard lead finish:
20 – 80 μ inches nickel /
6 μ inches palladium

c) Chip Size Dimensional Table

Chip Size			
X1	**Y1**	**X2**	**Y2**
2.36	2.36	0.75	0.67

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